## 2SD1485

## Silicon PNP triple diffusion planar type

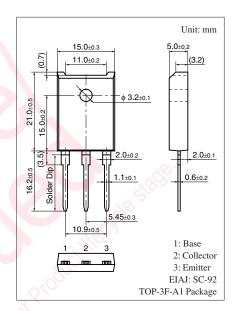
For high power amplification Complementary to 2SB1054

#### ■ Features

- ullet Excellent collector current  $I_C$  characteristics of forward current transfer ratio  $h_{FE}$
- Wide safe operation area
- High transition frequency f<sub>T</sub>
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings T<sub>C</sub> = 25°C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	100	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	100	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	I <sub>C</sub>	5	A	
Peak collector current	I <sub>CP</sub>	8	A	
Collector power dissipation	P <sub>C</sub>	60	W	
$T_a = 25^{\circ}C$		3.0		
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{\rm stg}$	-55 to +150	<b>℃</b> C	



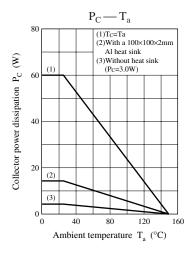
### ■ Electrical Characteristics T<sub>C</sub> = 25°C ± 3°C

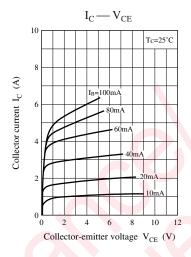
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	1.1		1.8	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 100 \text{ V}, I_{E} = 0$			50	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 3 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$	20			_
	h <sub>FE2</sub> *	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	60		200	
	h <sub>FE3</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	20			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.3 \text{ A}$			2.0	V
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		90		pF

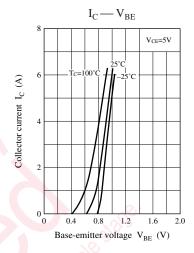
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

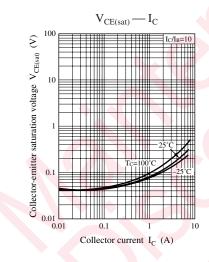
#### 2. \*: Rank classification

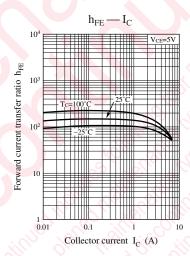
Rank	Q	Р
h <sub>FE2</sub>	60 to 120	100 to 200

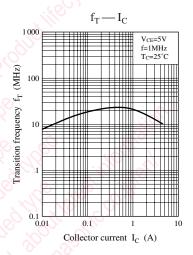


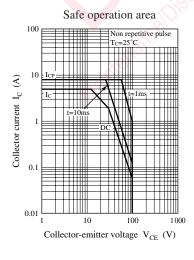


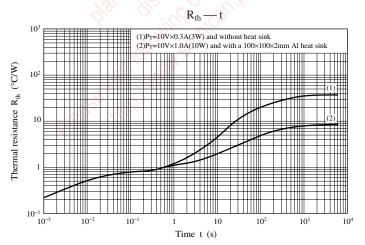












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